Technical Data *Green Products*
Data Sheet N1199, Rev. B

225CMQ015 SCHOTTKY RECTIFIER

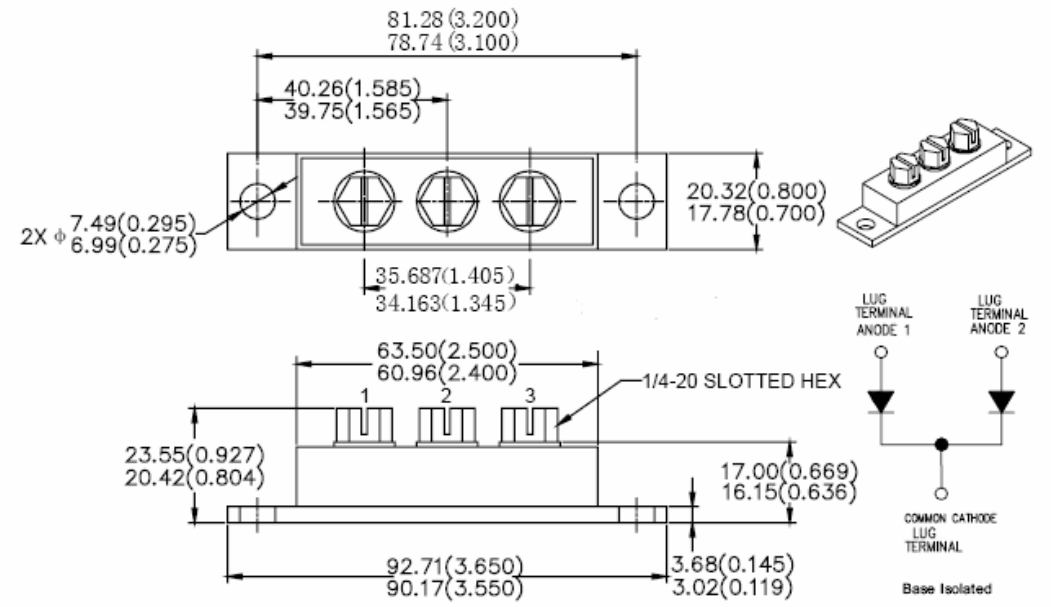
Applications:

- **Parallel switching power supply ● Free-Wheeling diodes ● Reverse battery protection**
- **Converters ● Redundant power subsystems**

Features:

- **125℃ T_J operation**
- **Center tap module**
- **High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance**
- **Low forward voltage drop**
- **High frequency operation**
- **Guard ring for enhanced ruggedness and long term reliability**
- **This is a Pb − Free Device**
- **All SMC parts are traceable to the wafer lot**
- **Additional testing can be offered upon request**

Mechanical Dimensions: In mm/Inches



Please Note: Anode 1 = Terminal 1; Anode 2 = Terminal 3; Common Cathode = Terminal 2
Suffix R Denotes for Reversed Polarity.

PRM4 (Isolated)

MARKING,MOLDING RESIN
Marking for 225CMQ015, 1st row SS YYWWL, 2nd row 225CMQ015
Where YY is the manufacture year
WW is the manufacture week code
L is the wafer's Lot Number
Molding resin
Epoxy resin UL:94V-0

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Maximum Ratings:

Characteristics	Symbol	Condition	Max.		Units
Peak Inverse Voltage	V_{RWM}	-	15		V
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle @T_C =74°C, rectangular wave form	110	per leg	A
			220	per device	
Max. Peak One Cycle Non-Repetitive Surge Current (per leg)	I_{FSM}	8.3 ms, half Sine pulse	2040		A
Non-Repetitive Avalanche Energy(peg leg)	E_{AS}	T_J=25℃,I_{AS}=2A,L=4.5mH	9		mJ
Repetitive Avalanche Current(peg leg)	I_{AR}	Current decaying linearly to zero in 1 µsec Frequency limited by T_J max. V_A=1.5× V_R typical	2		A

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop (per leg) *	V_{F1}	@ 110A, Pulse, T_J = 25 °C @ 220A, Pulse, T_J = 25 °C	0.38 0.49	V
	V_{F2}	@ 110A, Pulse, T_J = 125 °C @ 220A, Pulse, T_J = 125 °C	0.32 0.42	V
Max. Reverse Current (per leg) *	I_{R1}	@V_R = rated V_R T_J = 25 °C	40	mA
	I_{R2}	@V_R = rated V_R T_J = 125 °C	2000	mA
	I_{R3}	@V_R = rated V_R T_J = 100 °C	1780	mA
	I_{R4}	@V_R = rated V_R T_J = 100 °C	1080	mA
Max. Junction Capacitance	C_T	@V_R = 5V, T_C = 25 °C f_{SIG} = 1MHz	7700	pF
Typical Series Inductance (per leg)	L_S	Measured lead to lead 5 mm from package body	7.0	nH
Max. Voltage Rate of Change	dv/dt	-	10,000	V/µs

* Pulse Width < 300µs, Duty Cycle <2%

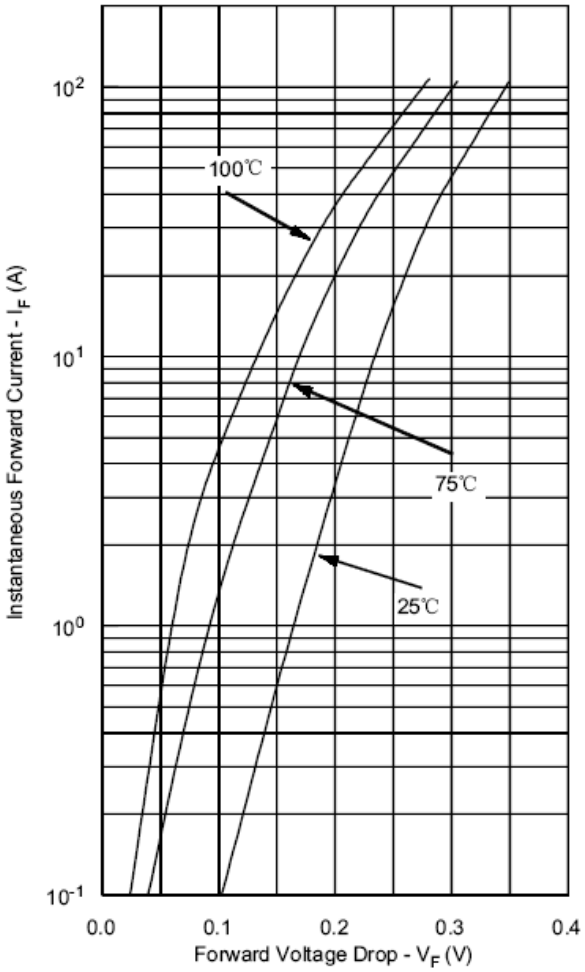
Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification		Units
Max. Junction Temperature	T_J	-	-55 to +125		°C
Max. Storage Temperature	T_{stg}	-	-55 to +125		°C
Maximum Thermal Resistance Junction to Case (per leg)	$R_{\theta JC}$	DC operation	0.70		°C/W
Maximum Thermal Resistance Junction to Case (per device)	$R_{\theta JC}$	DC operation	0.35		°C/W
Typical Thermal Resistance, case to Heat Sink	$R_{\theta cs}$	Mounting surface, smooth and greased	0.10		°C/W
Mounting Torque	T_M	-	Mounting Torque	24(min) 35(max)	Kg-cm
			Terminal Torque	35(min) 46(max)	
Approximate Weight	wt	-	79		g
Case Style	PRM4 (Isolated)				

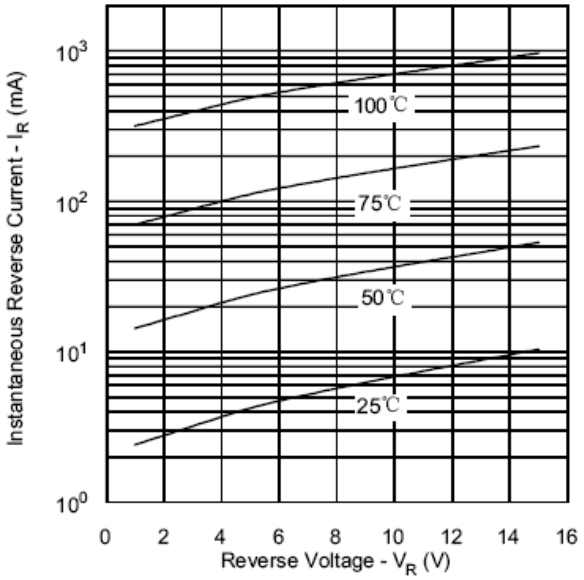
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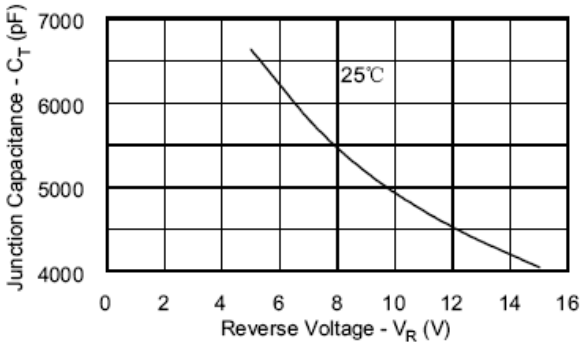
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



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